

NTE601 Silicon Varistor Temperature Compensating Diode

Features:

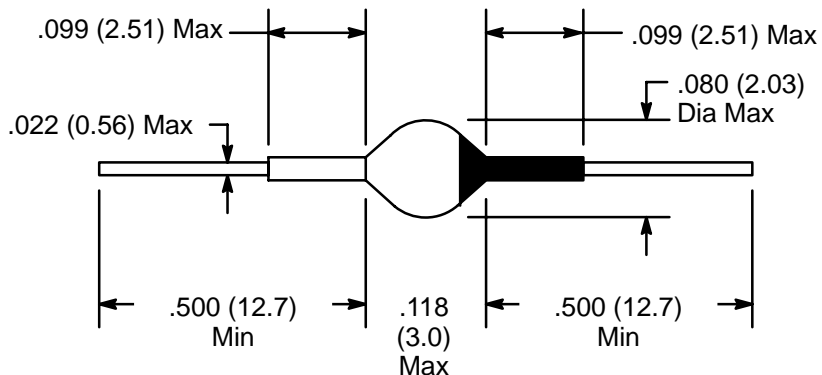
- High reliability planar chip and glass sealing
- Low I_R
- Large P_D

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Maximum Forward Current, I_{FM}	150mA
Reverse Voltage, V_R	6V
Power Dissipation, P_D	150mW
Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	-55° to +150°C

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Current	I_R	$V_R = 6V$	–	–	10	μA
Forward Voltage	V_F	$I_F = 1.5mA$	0.59	–	0.64	V
		$I_F = 50mA$	–	–	1.1	V
Forward Voltage Change with Respect to Temperature	$-\Delta V_F/\Delta T$	$I_F = 1.5mA$	–	2.0	–	mV/°C



Color Band Denotes Cathode